

**Atomic Layer Deposited Metal Oxide Bilayers for Metal-Insulator-Semiconductor
Photovoltaics – Supplemental Information**

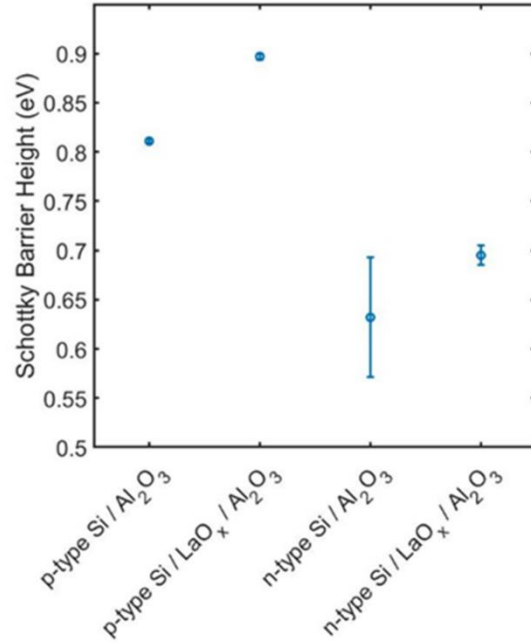


Fig. 1: Schottky barrier heights of various diode configurations as measured by Mott-Schottky analysis. The error bars represent the sample standard deviations.

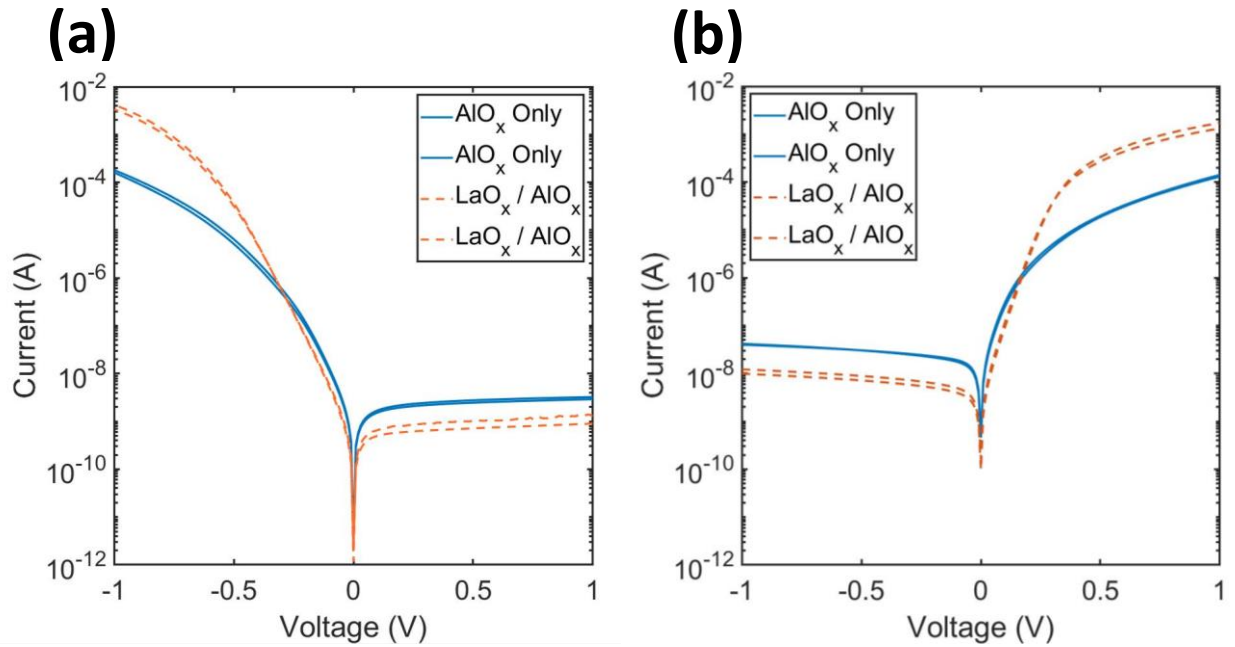


Fig. 2: Representative room temperature current-voltage curves from a) p-type and b) n-type Si diodes utilizing tunnel insulators comprising either AlO_x or LaO_x/AlO_x stacks with similar total thickness.

References

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